

METHODS FOR FORMING A THIN FILM ON AN INTEGRATED CIRCUIT
INCLUDING SOFT BAKING A SILICON ON GLASS FILM

ABSTRACT OF THE DISCLOSURE

Methods of forming a thin film on an integrated circuit substrate including a stepped portion are provided. A spin on glass (SOG) film is formed on the substrate including the stepped portion to fill a recess defined by the 5 stepped portion. The SOG film is soft baked at a temperature of less than 400°C. The soft baked SOG film is etched and an insulation film is formed on the etched SOG film. Methods of forming a trench isolation film including soft baking an SOG film are also provided.